Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	299	transistor same etch$3 same voltage same measur$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:11
L2	300	(transistor or BJT) same etch$3 same voltage same measur$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:22
L3	424	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:38
L4	2	"4314266".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:36
L5	2607	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same (voltage or resistance or conduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:39
L6	2037	5 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:43
L7	2393	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same (resistance or conduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:42
L8	80	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same (resistance or conduct$3) same measur$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:40

L9	2132	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same (voltage or conduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:47
L11	77	(SiC or "silicon carbide" or IdN or "indium nitride") same etch$3 same (voltage or conduct$3) same measur$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:44
L12	4368	(SiC or "silicon carbide" or "indium nitride") same (etch$3 or remov$3) same (voltage or conduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:48
L13	6	12 and "etch parameters"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:48
L14	624	(SiC or "silicon carbide" or "indium nitride") with (etch$3 or remov$3) with (voltage or conduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 10:50
L15	75	(SiC or "silicon carbide" or "indium nitride") with (etch$3 or remov$3) with (voltage or conductance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 11:49
L16	0	zeghbroeck-bart-j.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 11:50
L17	2	zeghbroeck-bart-j-van.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 11:50

L18	1	perez-Ivan.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 11:51
L19	1	torvik-john.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 11:51